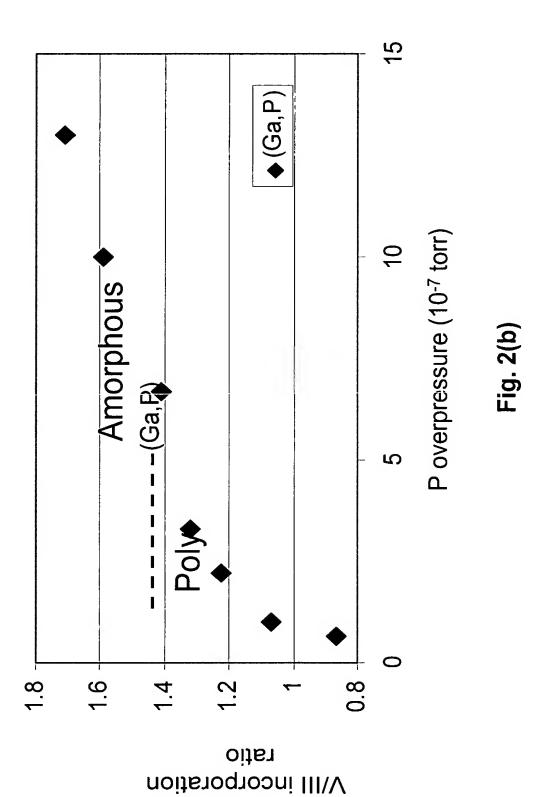
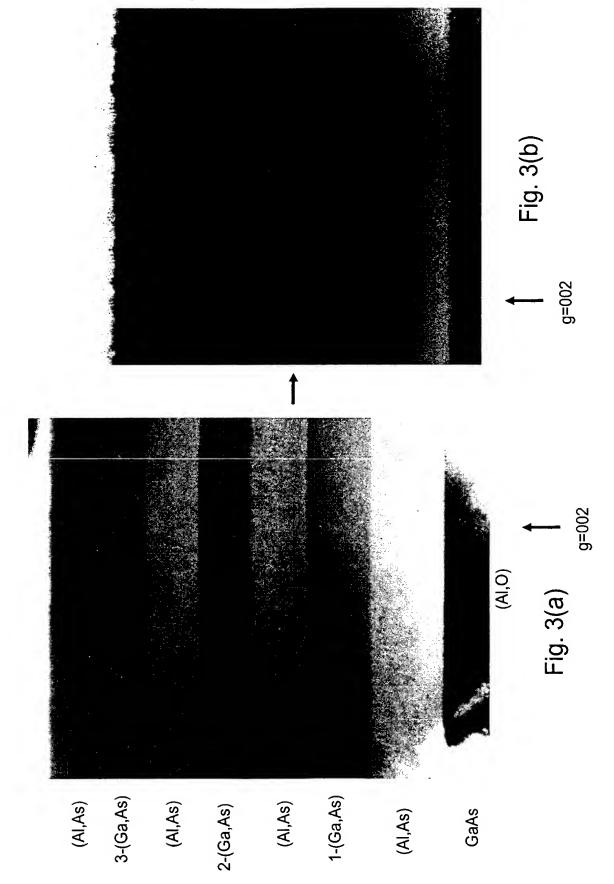
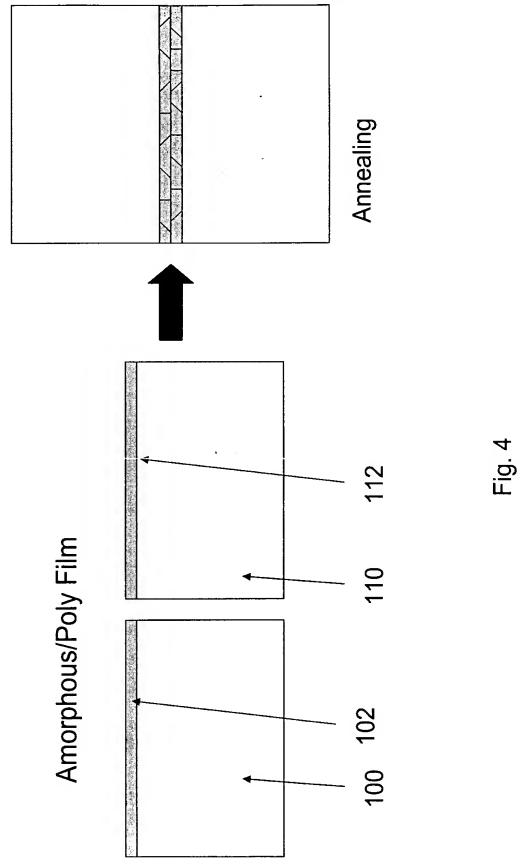


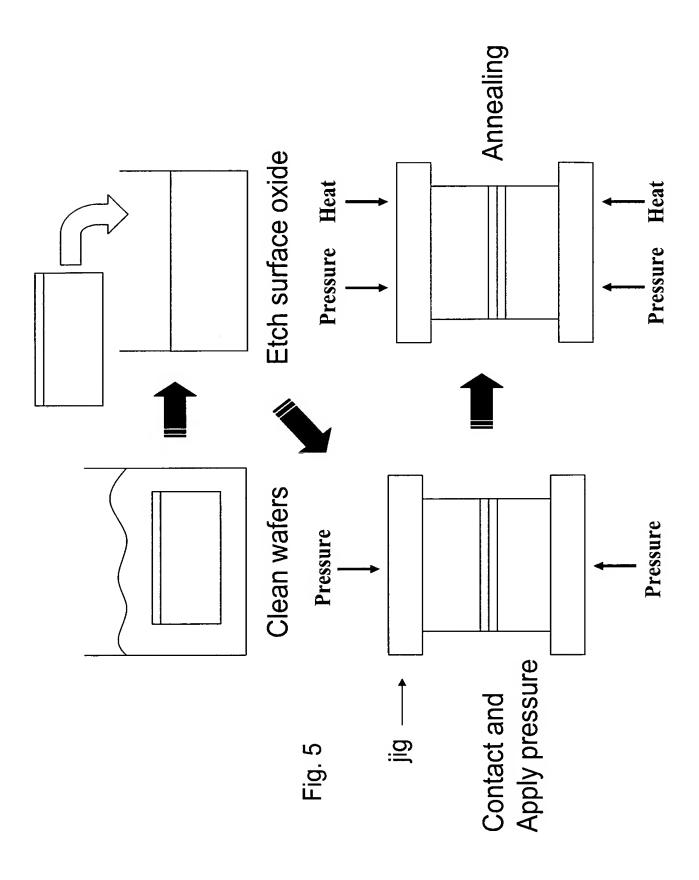
V/III incorporation ratio

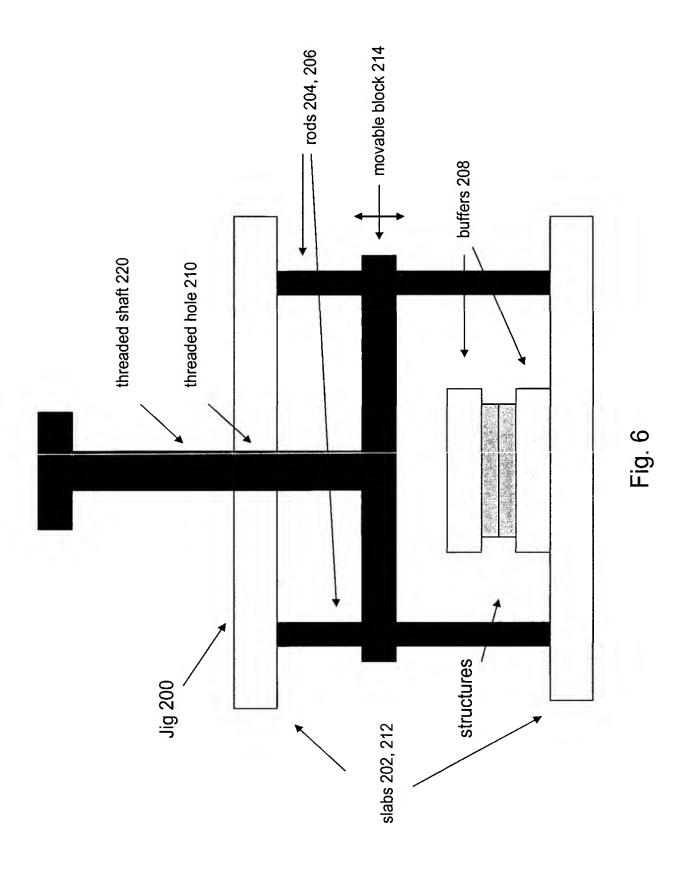


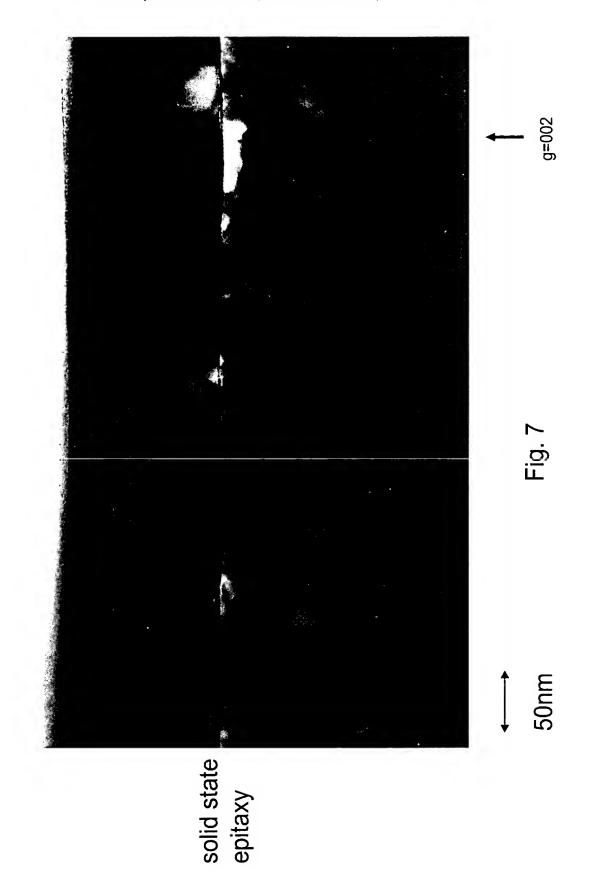
POLYCRYSTALLINE COMPOUND SEMICONDUCTORS
Inventor(s): Kuang-Chien Hsieh et al.
Attorney Docket No. 10322/57 (Client Ref. No. TF03009)











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Amorphous (Ga,P) bonding Anneal at 600 °C for 10 hrs

Polycrystalline (Ga,P) bonding

Fig. 8(b)

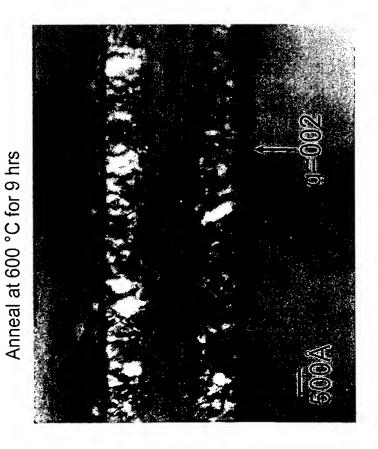
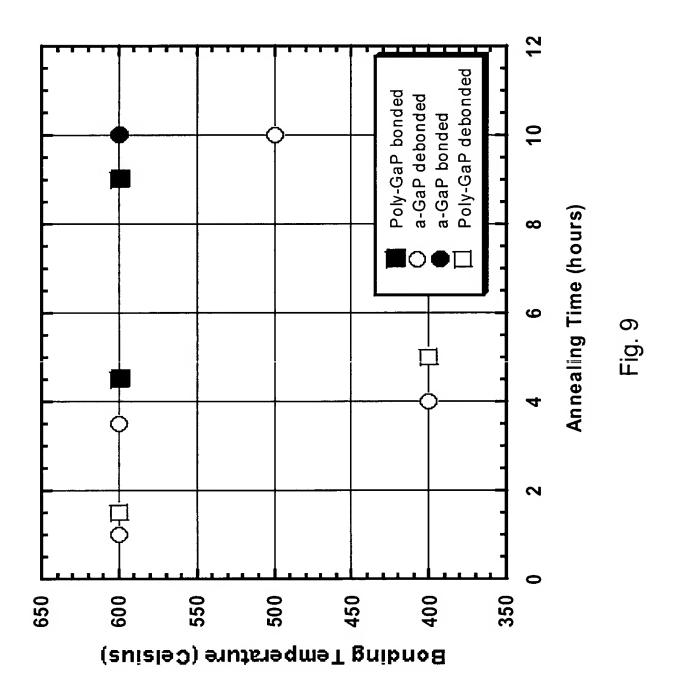
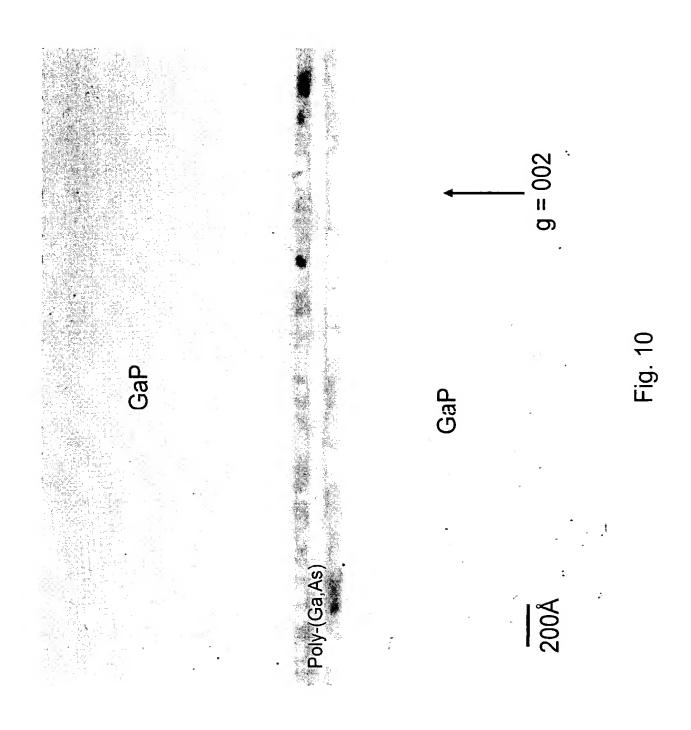
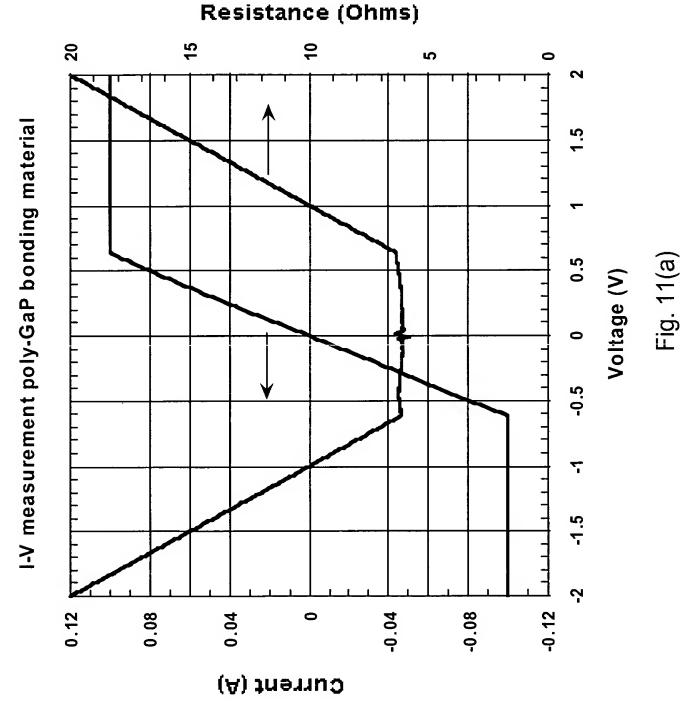
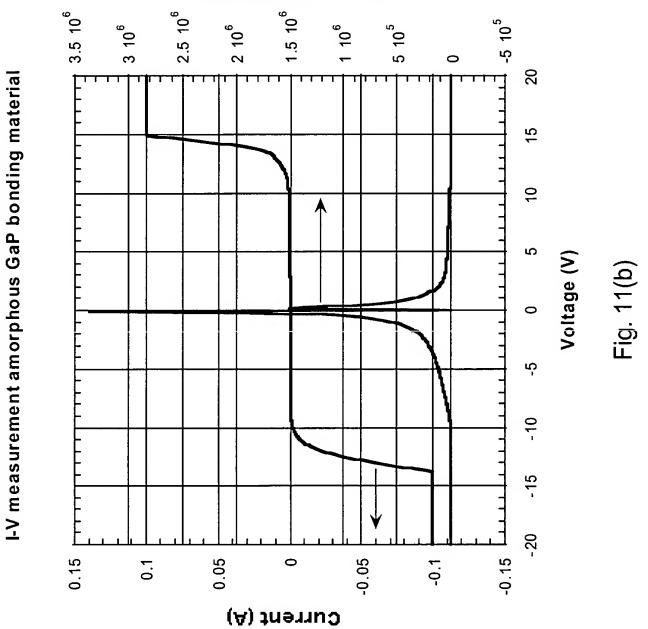


Fig. 8(a)

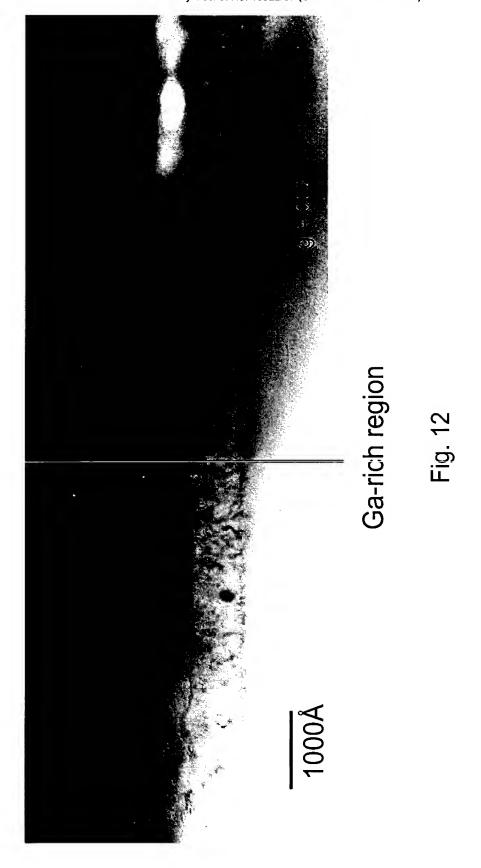


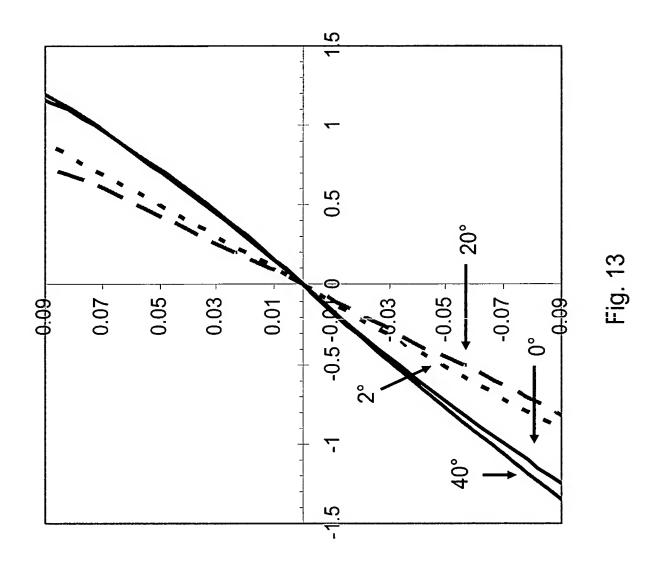


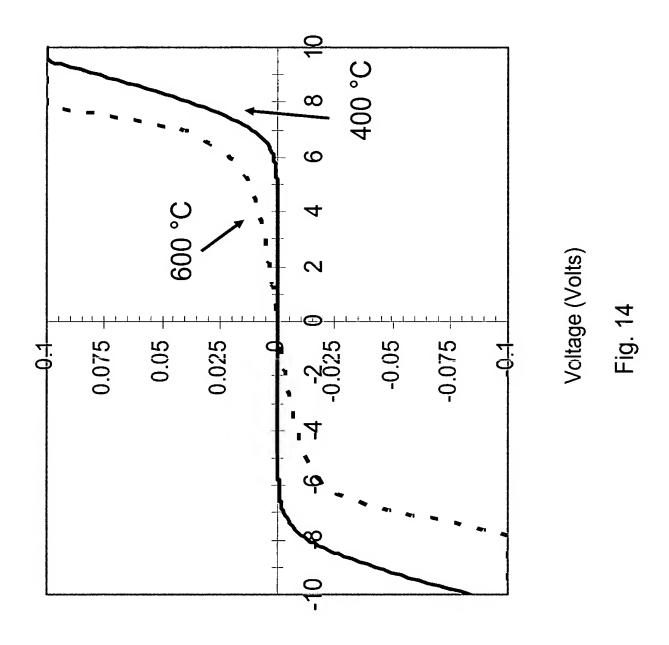




Resistance (Ohms)







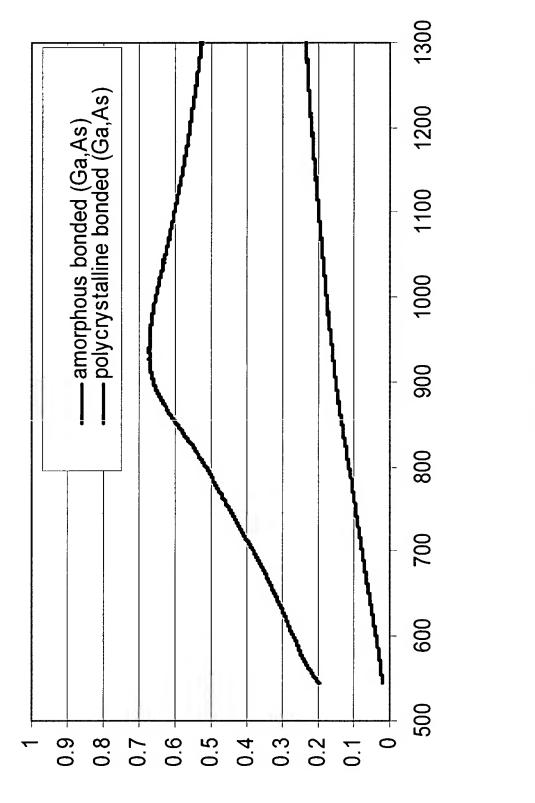


Fig. 15

